

PCT

WORLD INTELLECTUAL PROPERTY ORGANIZATION
International Bureau

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 6 : G11B 5/147	A1	(11) International Publication Number: WO 97/22965 (43) International Publication Date: 26 June 1997 (26.06.97)
(21) International Application Number: PCT/US96/18364 (22) International Filing Date: 15 November 1996 (15.11.96) (30) Priority Data: 08/573,888 18 December 1995 (18.12.95) US (71) Applicant: QUANTUM CORPORATION [US/US]; 500 McCarthy Boulevard, Milpitas, CA 95035 (US). (72) Inventor: MALLARY, Michael, L.; 113 Boylston Road, Berlin, MA 01503 (US). (74) Agents: HARRISON, David, B. et al.; Quantum Corporation, 500 McCarthy Boulevard, Milpitas, CA 95035 (US).	(81) Designated States: AU, CA, CN, JP, KR, SG, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report.</i>	

(54) Title: **LOW-INDUCTANCE THIN-FILM HEAD**

(57) Abstract

A low-inductance thin-film head (60) includes a flux barrier layer (52) of electrical conductive, non-magnetic material such as copper, gold and aluminum positioned on the head, wherein stray flux from the head is cut off by the flux barrier layer (52) to reduce the inductance of the head (60). Stray flux entering the barrier layer creates an eddy current in the layer which cuts off the stray flux paths of the head. The flux barrier layer (52) can be placed in various positions, including downstream or upstream of the head (60), or between the poles (14, 16), to improve the read or write performance of the head.

